

# Susanne Stemmer

## List of Publications by Year in descending order

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312  
papers

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citations

19608

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109  
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314  
all docs

314  
docs citations

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times ranked

13835  
citing authors

| #  | ARTICLE   | IF  | CITATIONS |
|----|---|-----|-----------|
| 1  | Resonant x-ray scattering method for measuring cation stoichiometry in BaSnO <sub>3</sub> thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, .             | 0.9 | 4         |
| 2  | Hall bar measurements of topological surface states of (001) cadmium arsenide thin films interfaced with superconductors. Physical Review Materials, 2022, 6, .                                       | 0.9 | 3         |
| 3  | Tracking Ultrafast Change of Multiterahertz Broadband Response Functions in a Photoexcited Dirac Semimetal Cd <sub>3</sub> As <sub>2</sub> Thin Film. Nano Letters, 2022, 22, 2358-2364.              | 4.5 | 9         |
| 4  | Hybrid oxide molecular beam epitaxy. , 2022, , 53-74.   |     | 0         |
| 5  | Controlling and visualizing Dirac physics in topological semimetal heterostructures. Science Advances, 2022, 8, .   | 4.7 | 6         |
| 6  | Similarity in the critical thicknesses for superconductivity and ferroelectricity in strained SrTiO <sub>3</sub> films. Applied Physics Letters, 2022, 121, 012601.                                   | 1.5 | 3         |
| 7  | Electron transport of perovskite oxide BaSnO <sub>3</sub> on (110) DyScO <sub>3</sub> substrate with channel-recess for ferroelectric field effect transistors. Applied Physics Letters, 2021, 118, . | 1.5 | 7         |
| 8  | Room-Temperature Spin Transport in Cd <sub>3</sub> As <sub>2</sub> . ACS Nano, 2021, 15, 5459-5466.   | 7.3 | 8         |
| 9  | Probing charge pumping and relaxation of the chiral anomaly in a Dirac semimetal. Science Advances, 2021, 7, .  | 4.7 | 16        |
| 10 | Superconductivity in magnetically doped SrTiO <sub>3</sub> . Applied Physics Letters, 2021, 118, .  | 1.5 | 11        |
| 11 | Controlling the symmetry of cadmium arsenide films by epitaxial strain. APL Materials, 2021, 9, .   | 2.2 | 5         |
| 12 | Quantum Hall effect of the topological insulator state of cadmium arsenide in Corbino geometry. Applied Physics Letters, 2021, 118, 261901.   | 1.5 | 1         |
| 13 | Thickness-independent transport in thin (001)-oriented cadmium arsenide films. Physical Review B, 2021, 104, .  | 1.1 | 6         |
| 14 | Interplay between Polar Distortions and Superconductivity in SrTiO <sub>3</sub> . Microscopy and Microanalysis, 2021, 27, 360-362.  | 0.2 | 1         |
| 15 | Molecular beam epitaxy of phase-pure antiperovskite Sr <sub>3</sub> SnO thin films. Applied Physics Letters, 2021, 119, .   | 1.5 | 4         |
| 16 | Role of locally polar regions in the superconductivity of $\text{SrTiO}_3$ . Physical Review Materials, 2021, 5, .  | 0.9 | 10        |
| 17 | Reducing surface depletion of superconducting SrTiO <sub>3</sub> films with EuTiO <sub>3</sub> capping layers. Applied Physics Letters, 2021, 119, .  | 1.5 | 5         |
| 18 | Detecting topological phase transitions in cadmium arsenide films via the transverse magnetoresistance. Applied Physics Letters, 2021, 119, .   | 1.5 | 8         |

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|----|--|-----|-----------|
| 19 | Nanoscale etching of perovskite oxides for field effect transistor applications. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2020, 38, .                                | 0.6 | 8         |
| 20 | Prospects of Terahertz Transistors with the Topological Semimetal Cadmium Arsenide. Advanced Electronic Materials, 2020, 6, 2000676.   | 2.6 | 11        |
| 21 | Polar Nanodomains in a Ferroelectric Superconductor. Nano Letters, 2020, 20, 6542-6547.  | 4.5 | 32        |
| 22 | Topological surface states in strained Dirac semimetal thin films. Physical Review B, 2020, 102, .   | 1.1 | 10        |
| 23 | Magnetoresistance effects in cadmium arsenide thin films. Applied Physics Letters, 2020, 117, .  | 1.5 | 1         |
| 24 | Order-Disorder Ferroelectric Transition of Strained $\text{SrTiO}_3$ . Physical Review Letters, 2020, 125, 087601.   | 2.9 | 40        |
| 25 | Probing the Polar Instability of Strained $\text{SrTiO}_3$ with HAADF-STEM. Microscopy and Microanalysis, 2020, 26, 2474-2476.   | 0.2 | 0         |
| 26 | Relating Crystal Symmetry to Topological Phases: Convergent Beam Electron Diffraction Studies of the Dirac Semimetal $\text{Cd}_3\text{As}_2$ . Microscopy and Microanalysis, 2020, 26, 3034-3037.           | 0.2 | 0         |
| 27 | Carrier mobilities of (001) cadmium arsenide films. APL Materials, 2020, 8, .  | 2.2 | 19        |
| 28 | Carbon impurity concentrations in $\text{BaSnO}_3$ films grown by molecular beam epitaxy using a tin oxide source. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 043405. | 0.9 | 1         |
| 29 | High-Current Perovskite Oxide $\text{BaTiO}_3/\text{BaSnO}_3$ Heterostructure Field Effect Transistors. IEEE Electron Device Letters, 2020, 41, 621-624.   | 2.2 | 8         |
| 30 | Efficient Terahertz Harmonic Generation with Coherent Acceleration of Electrons in the Dirac Semimetal $\text{Cd}_3\text{As}_2$ . Physical Review Letters, 2020, 124, 117402.                                | 2.9 | 97        |
| 31 | Possible signatures of mixed-parity superconductivity in doped polar $\text{SrTiO}_3$ films. Physical Review B, 2020, 101, .   | 1.1 | 34        |
| 32 | Hydrothermal growth of $\text{BaSnO}_3$ single crystals for wide bandgap applications. Journal of Crystal Growth, 2020, 536, 125529.   | 0.7 | 12        |
| 33 | Topological Insulator State and Collapse of the Quantum Hall Effect in a Three-Dimensional Dirac Semimetal Heterojunction. Physical Review X, 2020, 10, .  | 2.8 | 22        |
| 34 | Widely Tunable Optical and Thermal Properties of Dirac Semimetal $\text{Cd}_3\text{As}_2$ . Advanced Optical Materials, 2020, 8, 1901192.  | 3.6 | 27        |
| 35 | High Current Density $\text{SmTiO}_3/\text{SrTiO}_3$ Field-Effect Transistors. ACS Applied Electronic Materials, 2020, 2, 510-516.   | 2.0 | 6         |
| 36 | Stoichiometry control in molecular beam epitaxy of $\text{BaSnO}_3$ . Physical Review Materials, 2020, 4, .  | 0.9 | 8         |

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|----|--|-----|-----------|
| 37 | Correlating magnetic structure and magnetotransport in semimetal thin films of $\text{EuTiO}_3$ . Physical Review Materials, 2020, 4, .                | 0.9 | 1         |
| 38 | Field-effect transistors with the three-dimensional Dirac semimetal cadmium arsenide. Applied Physics Letters, 2019, 115, .                            | 1.5 | 12        |
| 39 | Probing the Local Lattice Distortions in Doped $\text{SrTiO}_3$ Using Quantitative STEM. Microscopy and Microanalysis, 2019, 25, 976-977.              | 0.2 | 0         |
| 40 | Velocity saturation in La-doped $\text{BaSnO}_3$ thin films. Applied Physics Letters, 2019, 115, .   | 1.5 | 9         |
| 41 | Absence of signatures of Weyl orbits in the thickness dependence of quantum transport in cadmium arsenide. Physical Review B, 2019, 99, .              | 1.1 | 12        |
| 42 | Enhancing superconductivity in $\text{SrTiO}_3$ films with strain. Science Advances, 2019, 5, eaaw0120.  | 4.7 | 130       |
| 43 | Controlling a Van Hove singularity and Fermi surface topology at a complex oxide heterostructure interface. Nature Communications, 2019, 10, 5534.     | 5.8 | 10        |
| 44 | Anisotropic magnetoresistance in the itinerant antiferromagnetic $\text{EuTiO}_3$ . Physical Review B, 2019, 99, .                                     | 1.1 | 31        |
| 45 | Design of Transistors Using High-Permittivity Materials. IEEE Transactions on Electron Devices, 2019, 66, 896-900.                                     | 1.6 | 33        |
| 46 | Basal-plane growth of cadmium arsenide by molecular beam epitaxy. Physical Review Materials, 2019, 3, .  | 0.9 | 19        |
| 47 | Surface states of strained thin films of the Dirac semimetal $\text{Cd}_3\text{As}_2$ . Physical Review Materials, 2019, 3, .                          | 0.9 | 18        |
| 48 | Point group symmetry of cadmium arsenide thin films determined by convergent beam electron diffraction. Physical Review Materials, 2019, 3, .          | 0.9 | 6         |
| 49 | Ferroelectric enhancement of superconductivity in compressively strained $\text{SrTiO}_3$ films. Physical Review Materials, 2019, 3, .                 | 0.9 | 4         |
| 50 | Lattice relaxations around individual dopant atoms in $\text{SrTiO}_3$ . Physical Review Materials, 2019, 3, .   | 0.9 | 6         |
| 51 | Soft phonons and ultralow lattice thermal conductivity in the Dirac semimetal $\text{Cd}_3\text{As}_2$ . Physical Review Research, 2019, 1, .          | 1.3 | 26        |
| 52 | Thickness dependence of the quantum Hall effect in films of the three-dimensional Dirac semimetal $\text{Cd}_3\text{As}_2$ . APL Materials, 2018, 6, . | 2.2 | 55        |
| 53 | Quasistatic antiferromagnetism in the quantum wells of $\text{SmTiO}_3/\text{SrTiO}_3$ heterostructures. Npj Quantum Materials, 2018, 3, .             | 1.8 | 8         |
| 54 | Non-Fermi liquids in oxide heterostructures. Reports on Progress in Physics, 2018, 81, 062502.   | 8.1 | 21        |

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|----|---|-----|-----------|
| 55 | Observation of the Quantum Hall Effect in Confined Films of the Three-Dimensional Dirac Semimetal $Cd_3As_2$ . Physical Review Letters, 2016, 116, 086801.  | 2.9 | 144       |
| 56 | Electron spin Hall effect in a strained Dirac semimetal $Cd_3As_2$ . Applied Physics Letters, 2016, 109, 162107.  | 1.1 | 13        |
| 57 | Octahedral tilt independent magnetism in confined $GdTiO_3$ films. Applied Physics Letters, 2018, 112, 132407.  | 1.5 | 2         |
| 58 | Two-dimensional Dirac fermions in thin films of $Cd_3As_2$ . Physical Review Letters, 2016, 116, 086801.  | 1.1 | 42        |
| 59 | Carrier density control of magnetism and Berry phases in doped $EuTiO_3$ . APL Materials, 2018, 6, .  | 2.2 | 24        |
| 60 | Spontaneous Hall effects in the electron system at the $SmTiO_3/EuTiO_3$ interface. APL Materials, 2018, 6, .   | 2.2 | 22        |
| 61 | Resolving interfacial charge transfer in titanate superlattices using resonant x-ray reflectometry. Physical Review Materials, 2018, 2, .                   | 0.9 | 1         |
| 62 | Nitrogen surface passivation of the Dirac semimetal $Cd_3As_2$ . Applied Physics Letters, 2017, 110, .  | 0.9 | 16        |
| 63 | Electric field effect near the metal-insulator transition of a two-dimensional electron system in $SrTiO_3$ . Applied Physics Letters, 2017, 110, .         | 1.5 | 26        |
| 64 | Potential Fluctuations at Low Temperatures in Mesoscopic-Scale $SmTiO_3/SrTiO_3/SmTiO_3$ Quantum Well Structures. ACS Nano, 2017, 11, 3760-3766.            | 7.3 | 1         |
| 65 | $BaTiO_3/SrTiO_3$ heterostructures for ferroelectric field effect transistors. Applied Physics Letters, 2017, 110, .  | 1.5 | 33        |
| 66 | HAADF-STEM Study of MBE-Grown Dirac Semimetal $Cd_3As_2$ . Microscopy and Microanalysis, 2017, 23, 1480-1481.   | 0.2 | 0         |
| 67 | Probing Disorder in MBE-grown Oxide Films Using Quantitative STEM. Microscopy and Microanalysis, 2017, 23, 1578-1579.                                       | 0.2 | 0         |
| 68 | Response of the Lattice across the Filling-Controlled Mott Metal-Insulator Transition of a Rare Earth Titanate. Physical Review Letters, 2017, 119, 186803. | 2.9 | 7         |
| 69 | Disorder versus two transport lifetimes in a strongly correlated electron liquid. Scientific Reports, 2017, 7, 10312.                                       | 1.6 | 2         |
| 70 | Evidence of a topological Hall effect in $Eu_1-xSm_xTiO_3$ . Applied Physics Letters, 2017, 111, .  | 1.5 | 52        |
| 71 | Novel Metal-Insulator Transition at the $SmTiO_3/SrTiO_3$ interface. Physical Review Letters, 2017, 118, 076803.  | 2.9 | 39        |
| 72 | Negative magnetoresistance due to conductivity fluctuations in films of the topological semimetal $Cd_3As_2$ . Applied Physics Letters, 2017, 110, .        | 1.1 | 68        |

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|----|---|-----|-----------|
| 73 | Imaging Point Defects in Complex Oxides Using Quantitative STEM. Microscopy and Microanalysis, 2017, 23, 1568-1569.   | 0.2 | 0         |
| 74 | Effect of BST film thickness on the performance of tunable interdigital capacitors grown by MBE. Applied Physics Letters, 2017, 111, 262903.  | 1.5 | 15        |
| 75 | Growth of strontium ruthenate films by hybrid molecular beam epitaxy. APL Materials, 2017, 5, 096101.   | 2.2 | 15        |
| 76 | Key role of lattice symmetry in the metal-insulator transition of NdNiO <sub>3</sub> films. Scientific Reports, 2016, 6, 23652.   | 1.6 | 33        |
| 77 | Direct Observation of Sr Vacancies in $\text{SrTiO}_3$ by Quantitative Scanning Transmission Electron Microscopy. Physical Review X, 2016, 6, .                                       | 2.8 | 26        |
| 78 | Large electron concentration modulation using capacitance enhancement in SrTiO <sub>3</sub> /SmTiO <sub>3</sub> Fin-field effect transistors. Applied Physics Letters, 2016, 108, .   | 1.5 | 4         |
| 79 | (Ba,Sr)TiO <sub>3</sub> tunable capacitors with RF commutation quality factors exceeding 6000. Applied Physics Letters, 2016, 109, 112902.  | 1.5 | 29        |
| 80 | Carrier density independent scattering rate in SrTiO <sub>3</sub> -based electron liquids. Scientific Reports, 2016, 6, 20865.  | 1.6 | 32        |
| 81 | Role of film stoichiometry and interface quality in the performance of (Ba,Sr)TiO <sub>3</sub> tunable capacitors with high figures of merit. Applied Physics Letters, 2016, 109, .   | 1.5 | 17        |
| 82 | Structure and optical band gaps of (Ba,Sr)SnO <sub>3</sub> films grown by molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, . | 0.9 | 45        |
| 83 | Band alignments between SmTiO <sub>3</sub> , GdTiO <sub>3</sub> , and SrTiO <sub>3</sub> . Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .        | 0.9 | 6         |
| 84 | Conduction band edge effective mass of La-doped BaSnO <sub>3</sub> . Applied Physics Letters, 2016, 108, .  | 1.5 | 39        |
| 85 | Molecular beam epitaxy of Cd <sub>3</sub> As <sub>2</sub> on a III-V substrate. APL Materials, 2016, 4, .   | 2.2 | 68        |
| 86 | Two-port tunable interdigital capacitors fabricated on low-loss MBE-grown Ba <sub>0.29</sub> Sr <sub>0.71</sub> TiO <sub>3</sub> . , 2016, , .  |     | 1         |
| 87 | High-mobility BaSnO <sub>3</sub> grown by oxide molecular beam epitaxy. APL Materials, 2016, 4, .   | 2.2 | 181       |
| 88 | Probing the Metal-Insulator Transition in $\text{BaTiO}_3$ by Electrostatic Doping. Physical Review Letters, 2016, 117, 037602.   | 2.9 | 33        |
| 89 | Interface-Driven Ferromagnetism within the Quantum Wells of a Rare Earth Titanate Superlattice. Physical Review Letters, 2016, 117, 037205.   | 2.9 | 12        |
| 90 | Pseudogaps and Emergence of Coherence in Two-Dimensional Electron Liquids in $\text{SrTiO}_3$ . Physical Review Letters, 2016, 117, 046402.   | 2.9 | 12        |

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|-----|---|-----|-----------|
| 91  | Energetic, spatial, and momentum character of the electronic structure at a buried interface: The two-dimensional electron gas between two metal oxides. <i>Physical Review B</i> , 2016, 93, .   | 1.1 | 29        |
| 92  | Depth-Resolved Composition and Electronic Structure of Buried Layers and Interfaces in a LaNiO <sub>3</sub> /SrTiO <sub>3</sub> Superlattice from Soft- and Hard- X-ray Standing-Wave Angle-Resolved Photoemission. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2016, 211, 70-81. | 0.8 | 9         |
| 93  | Separation of transport lifetimes in $\text{SrTiO}_3$ -based two-dimensional electron liquids. <i>Physical Review B</i> , 2015, 91, .   | 1.1 | 22        |
| 94  | Dielectric response of metal/SrTiO <sub>3</sub> /two-dimensional electron liquid heterostructures. <i>Applied Physics Letters</i> , 2015, 107, 072905.  | 1.5 | 3         |
| 95  | Variable-angle high-angle annular dark-field imaging: application to three-dimensional dopant atom profiling. <i>Scientific Reports</i> , 2015, 5, 12419.   | 1.6 | 29        |
| 96  | Gaps and pseudogaps in perovskite rare earth nickelates. <i>APL Materials</i> , 2015, 3, 062503.  | 2.2 | 30        |
| 97  | Observation by resonant angle-resolved photoemission of a critical thickness for 2-dimensional electron gas formation in SrTiO <sub>3</sub> embedded in GdTiO <sub>3</sub> . <i>Applied Physics Letters</i> , 2015, 107, 231602.  | 1.5 | 9         |
| 98  | Ferroelectric transition in compressively strained SrTiO <sub>3</sub> thin films. <i>Applied Physics Letters</i> , 2015, 107, .   | 1.5 | 41        |
| 99  | <i>In-situ</i> nitrogen plasma passivation of Al <sub>2</sub> O <sub>3</sub> /GaN interface states. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015, 33, .   | 0.9 | 14        |
| 100 | Tuning bad metal and non-Fermi liquid behavior in a Mott material: Rare-earth nickelate thin films. <i>Science Advances</i> , 2015, 1, e1500797.  | 4.7 | 99        |
| 101 | 0.5 V Supply Voltage Operation of In <sub>0.65</sub> Ga <sub>0.35</sub> As/GaAs <sub>0.4</sub> Sb <sub>0.6</sub> Tunnel FET. <i>IEEE Electron Device Letters</i> , 2015, 36, 20-22.   | 2.2 | 48        |
| 102 | Determination of the Mott-Hubbard gap in GdTiO <sub>3</sub> . <i>Physical Review B</i> , 2015, 92, .  | 1.1 | 15        |
| 103 | Tailoring resistive switching in Pt/SrTiO <sub>3</sub> junctions by stoichiometry control. <i>Scientific Reports</i> , 2015, 5, 11079.  | 1.6 | 37        |
| 104 | Limitations to the room temperature mobility of two- and three-dimensional electron liquids in SrTiO <sub>3</sub> . <i>Applied Physics Letters</i> , 2015, 106, .   | 1.5 | 51        |
| 105 | Small hole polarons in rare-earth titanates. <i>Applied Physics Letters</i> , 2015, 106, .  | 1.5 | 22        |
| 106 | The electrochemical impact on electrostatic modulation of the metal-insulator transition in nickelates. <i>Applied Physics Letters</i> , 2015, 106, .   | 1.5 | 26        |
| 107 | Two-dimensional electron liquid at the (111) SmTiO <sub>3</sub> /SrTiO <sub>3</sub> interface. <i>Applied Physics Letters</i> , 2015, 106, .  | 1.5 | 20        |
| 108 | Correlation between stoichiometry, strain, and metal-insulator transitions of NdNiO <sub>3</sub> films. <i>Applied Physics Letters</i> , 2015, 106, .   | 1.5 | 58        |

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|-----|---|------|-----------|
| 109 | Emergence of room-temperature ferroelectricity at reduced dimensions. <i>Science</i> , 2015, 349, 1314-1317.  | 6.0  | 259       |
| 110 | Formation of InGaAs fins by atomic layer epitaxy on InP sidewalls. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 065503.   | 0.8  | 3         |
| 111 | Alleviating polarity-conflict at the heterointerfaces of KTaO <sub>3</sub> /GdScO <sub>3</sub> polar complex-oxides. <i>Applied Physics Letters</i> , 2014, 105, .                                      | 1.5  | 12        |
| 112 | Modulation of over $10^{14}$ cm <sup>-2</sup> electrons in SrTiO <sub>3</sub> /GdTlO <sub>3</sub> heterostructures. <i>Applied Physics Letters</i> , 2014, 104, .                                       | 1.5  | 38        |
| 113 | Extremely scaled high- $k$ /In <sub>0.53</sub> Ga <sub>0.47</sub> As gate stacks with low leakage and low interface trap densities. <i>Journal of Applied Physics</i> , 2014, 116, 124104.              | 1.1  | 23        |
| 114 | Intrinsic Mobility Limiting Mechanisms in Lanthanum-Doped Strontium Titanate. <i>Physical Review Letters</i> , 2014, 112, .   | 2.9  | 90        |
| 115 | Au-gated SrTiO <sub>3</sub> field-effect transistors with large electron concentration and current modulation. <i>Applied Physics Letters</i> , 2014, 105, .  | 1.5  | 19        |
| 116 | Highly Scalable Raised Source/Drain InAs Quantum Well MOSFETs Exhibiting $I_{ON}/I_{OFF} = 482$ and $I_{ON}/I_{OFF} = 100$ at $V_{DD} = 0.5$ V. <i>IEEE Electron Device Letters</i> , 2014, 35, 121001. | 2.2  | 25        |
| 117 | Scaled ZrO <sub>2</sub> dielectrics for In <sub>0.53</sub> Ga <sub>0.47</sub> As gate stacks with low interface trap densities. <i>Applied Physics Letters</i> , 2014, 104, .                           | 1.5  | 21        |
| 118 | Nanostructure investigations of nonlinear differential conductance in NdNiO <sub>3</sub> thin films. <i>Physical Review B</i> , 2014, 90, .   | 1.1  | 6         |
| 119 | Surface reconstructions in molecular beam epitaxy of SrTiO <sub>3</sub> . <i>Applied Physics Letters</i> , 2014, 105, .   | 1.5  | 40        |
| 120 | Two-Dimensional Electron Gases at Complex Oxide Interfaces. <i>Annual Review of Materials Research</i> , 2014, 44, 151-171.   | 4.3  | 154       |
| 121 | Element Specific Monolayer Depth Profiling. <i>Advanced Materials</i> , 2014, 26, 6554-6559.  | 11.1 | 58        |
| 122 | Correlation between metal-insulator transitions and structural distortions in high-electron-density SrTiO <sub>3</sub> quantum wells. <i>Physical Review B</i> , 2014, 89, .                            | 1.1  | 38        |
| 123 | Quantum critical behaviour in confined SrTiO <sub>3</sub> quantum wells embedded in antiferromagnetic SmTiO <sub>3</sub> . <i>Nature Communications</i> , 2014, 5, 4258.                                | 5.8  | 48        |
| 124 | Resistive switching and its suppression in Pt/Nb:SrTiO <sub>3</sub> junctions. <i>Nature Communications</i> , 2014, 5, 3990.  | 5.8  | 167       |
| 125 | S5-H6: Leakage current suppression in InGaAs-channel MOSFETs: Recessed InP source/drain spacers and InP channel caps. , 2014, , .   |      | 1         |
| 126 | Interface-induced magnetism in perovskite quantum wells. <i>Physical Review B</i> , 2013, 88, .   | 1.1  | 56        |



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|-----|---|-----|-----------|
| 127 | Magnetism and local structure in low-dimensional Mott insulating GdTiO $\times 3$ . Physical Review B, 2013, 88, .  | 1.1 | 22        |
| 128 | Three-Dimensional Imaging of Individual Dopant Atoms in SrTiO $\times 3$ . Physical Review Letters, 2013, 111, 266101.  | 2.9 | 86        |
| 129 | Nitrogen-passivated dielectric/InGaAs interfaces with sub-nm equivalent oxide thickness and low interface trap densities. Applied Physics Letters, 2013, 102, .   | 1.5 | 73        |
| 130 | High transconductance surface channel In $\times 0.53$ Ga $\times 0.47$ As MOSFETs using MBE source-drain regrowth and surface digital etching. , 2013, , .   |     | 4         |
| 131 | Symmetry Lowering in Extreme-Electron-Density Perovskite Quantum Wells. Physical Review Letters, 2013, 110, 256401.   | 2.9 | 51        |
| 132 | Spin injection and detection in lanthanum- and niobium-doped SrTiO $\times 3$ using the Hanle technique. Nature Communications, 2013, 4, 2134.  | 5.8 | 46        |
| 133 | La-doped SrTiO $\times 3$ films with large cryogenic thermoelectric power factors. Applied Physics Letters, 2013, 102, .  | 1.5 | 83        |
| 134 | Quantum confinement in oxide quantum wells. MRS Bulletin, 2013, 38, 1032-1039.  | 1.7 | 40        |
| 135 | Structural origins of the properties of rare earth nickelate superlattices. Physical Review B, 2013, 87, .  | 1.1 | 64        |
| 136 | Growth window and effect of substrate symmetry in hybrid molecular beam epitaxy of a Mott insulating rare earth titanate. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .                             | 0.9 | 48        |
| 137 | Subband structure of two-dimensional electron gases in SrTiO $\times 3$ . Applied Physics Letters, 2013, 103, 212103.   | 1.5 | 10        |
| 138 | Two-dimensional electron gas in a modulation-doped SrTiO $\times 3$ /Sr(Ti, Zr)O $\times 3$ heterostructure. Applied Physics Letters, 2013, 103, 082120.  | 1.5 | 29        |
| 139 | Reduction of leakage current in In $\times 0.53$ Ga $\times 0.47$ As channel metal-oxide-semiconductor field-effect-transistors using AlAs $\times 0.56$ Sb $\times 0.44$ confinement layers. Applied Physics Letters, 2013, 103, 203502. | 1.5 | 8         |
| 140 | Conduction-band edge and Shubnikov-de Haas effect in low-electron-density SrTiO $\times 3$ . Physical Review B, 2013, 88, .   | 1.1 | 57        |
| 141 | High performance raised source/drain InAs/In $\times 0.53$ Ga $\times 0.47$ As channel metal-oxide-semiconductor field-effect-transistors with reduced leakage using a vertical spacer. Applied Physics Letters, 2013, 103, .             | 1.5 | 40        |
| 142 | High-density Two-Dimensional Small Polaron Gas in a Delta-Doped Mott Insulator. Scientific Reports, 2013, 3, 3284.  | 1.6 | 25        |
| 143 | Influence of plasma-based in-situ surface cleaning procedures on HfO $\times 2$ /In $\times 0.53$ Ga $\times 0.47$ As gate stack properties. Journal of Applied Physics, 2013, 114, 154108.   | 1.1 | 21        |
| 144 | Temperature-dependence of the Hall coefficient of NdNiO $\times 3$ thin films. Applied Physics Letters, 2013, 103, 182105.  | 1.5 | 33        |

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|-----|--|-----|-----------|
| 145 | Electric field-tunable Ba <sub>x</sub> Sr <sub>1-x</sub> TiO <sub>3</sub> films with high figures of merit grown by molecular beam epitaxy. Applied Physics Letters, 2012, 101, .  | 1.5 | 44        |
| 146 | Seebeck coefficient of a quantum confined, high-electron-density electron gas in SrTiO <sub>3</sub> . Applied Physics Letters, 2012, 100, 161601.  | 1.5 | 15        |
| 147 | Quantum oscillations from a two-dimensional electron gas at a Mott/band insulator interface. Applied Physics Letters, 2012, 101, .   | 1.5 | 33        |
| 148 | Modulation doping to control the high-density electron gas at a polar/non-polar oxide interface. Applied Physics Letters, 2012, 101, .   | 1.5 | 17        |
| 149 | Nanoscale quantification of octahedral tilts in perovskite films. Applied Physics Letters, 2012, 100, .  | 1.5 | 59        |
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